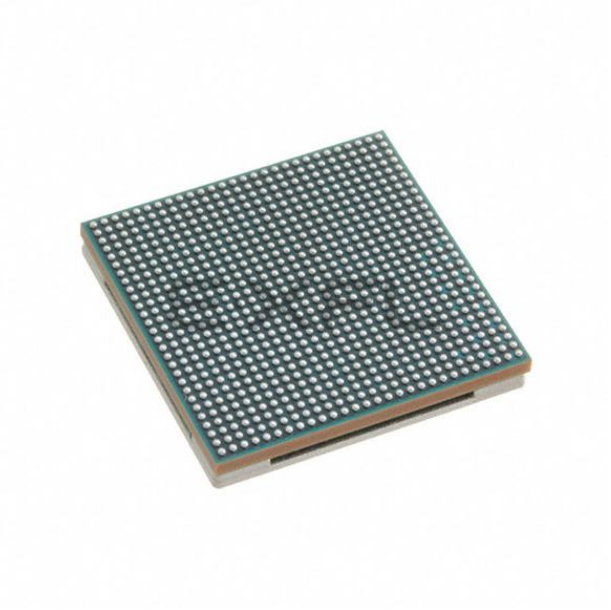
Microchip Technology - MPF300T-1FCG784E Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	388
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	784-BBGA, FCBGA
Supplier Device Package	784-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300t-1fcg784e

2 Overview

This datasheet describes PolarFire® FPGA device characteristics with industrial temperature range (–40 °C to 100 °C T_J) and extended commercial temperature range (0 °C to 100 °C T_J). The devices are provided with a standard speed grade (STD) and a –1 speed grade with higher performance. The FPGA core supply V_{DD} can operate at 1.0 V for lower-power or 1.05 V for higher performance. Similarly, the transceiver core supply V_{DDA} can also operate at 1.0 V or 1.05 V. Users select the core operating voltage while creating the Libero project.

5 Silicon Status

There are three silicon status levels:

- **Advanced**—initial estimated information based on simulations
- **Preliminary**—information based on simulation and/or initial characterization
- **Production**—final production silicon data

The following table shows the status of the PolarFire FPGA device.

Table 2 • PolarFire FPGA Silicon Status

Device	Silicon Status
MPF100T, TL, TS, TLS	Preliminary
MPF200T, TL, TS, TLS	Preliminary
MPF300T, TL, TS, TLS	Preliminary
MPF500T, TL, TS, TLS	Preliminary

Parameter	Symbol	Min	Typ	Max	Unit
Transceiver TX and RX lanes supply at 1.05 V mode (when any lane rate is greater than 10.3125 Gbps)[1]	V_{DDA}	1.02	1.05	1.08	V
Programming and HSIO receiver supply	V_{DD18}	1.71	1.80	1.89	V
FPGA core and FPGA PLL high-voltage supply	V_{DD25}	2.425	2.50	2.575	V
Transceiver PLL high-voltage supply	V_{DDA25}	2.425	2.50	2.575	V
Transceiver reference clock supply –3.3 V nominal	$V_{DD\_XCVR\_CLK}$	3.135	3.3	3.465	V
Transceiver reference clock supply –2.5 V nominal	$V_{DD\_XCVR\_CLK}$	2.375	2.5	2.625	V
Global V_{REF} for transceiver reference clocks[3]	$XCVR_{VREF}$	Ground		$V_{DD\_XCVR\_CLK}$	V
HSIO DC I/O supply. Allowed nominal options: 1.2 V, 1.35 V, 1.5 V, and 1.8 V[4]	V_{DDIx}	1.14	Various	1.89	V
GPIO DC I/O supply. Allowed nominal options: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V[2,4]	V_{DDIx}	1.14	Various	3.465	V
Dedicated I/O DC supply for JTAG and SPI (GPIO Bank 3). Allowed nominal options: 1.8 V, 2.5 V, and 3.3 V	V_{DDI3}	1.71	Various	3.465	V
GPIO auxiliary supply for I/O bank x with V_{DDIx} = 3.3 V nominal[2,4]	V_{DDAUXx}	3.135	3.3	3.465	V
GPIO auxiliary supply for I/O bank x with V_{DDIx} = 2.5 V nominal or lower[2,4]	V_{DDAUXx}	2.375	2.5	2.625	V
Extended commercial temperature range	T_J	0		100	°C
Industrial temperature range	T_J	–40		100	°C
Extended commercial programming temperature range	T_{PRG}	0		100	°C
Industrial programming temperature range	T_{PRG}	–40		100	°C

1. V_{DD} and V_{DDA} can independently operate at 1.0 V or 1.05 V nominal. These supplies are not dynamically adjustable.
2. For GPIO buffers where I/O bank is designated as bank number, if V_{DDIx} is 2.5 V nominal or 3.3 V nominal, V_{DDAUXx} must be connected to the V_{DDIx} supply for that bank. If V_{DDIx} for a given GPIO bank is <2.5 V nominal, V_{DDAUXx} per I/O bank must be powered at 2.5 V nominal.
3. $XCVR_{VREF}$ globally sets the reference voltage of the transceiver's single-ended reference clock input buffers. It is typically near $V_{DD\_XCVR\_CLK}/2$ V but is allowed in the specified range.
4. The power supplies for a given I/O bank x are shown as VDDIx and VDDAUXx.

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{IL} Min (V)	V_{IL} Max (V)	V_{IH} Min (V)	V_{IH}[1] Max (V)
SSTL135I	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
SSTL135II	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL15I	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575
HSTL15II	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575
HSTL135I	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL135II	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
HSTL12II	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
HSUL18I	1.71	1.8	1.89	–0.3	0.3 × V_{DDI}	0.7 × V_{DDI}	1.89
HSUL18II	1.71	1.8	1.89	–0.3	0.3 × V_{DDI}	0.7 × V_{DDI}	1.89
HSUL12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
POD12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.08	V_{REF} + 0.08	1.26
POD12II	1.14	1.2	1.26	–0.3	V_{REF} – 0.08	V_{REF} + 0.08	1.26

1. GPIO V_{IH} max is 3.45 V with PCI clamp diode turned off regardless of mode, that is, over-voltage tolerant.
2. For external stub-series resistance. This resistance is on-die for GPIO.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

Table 17 • Complementary Differential DC Output Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{OL} Min (V)	V_{OL} Max (V)	V_{OH}[1,3] Min (V)	I_{OL}[2] Min (mA)	I_{OH}[2] Min (mA)
SSTL25I	2.375	2.5	2.625		V_{TT} – 0.608	V_{TT} + 0.608	8.1	8.1
SSTL25II	2.375	2.5	2.625		V_{TT} – 0.810	V_{TT} + 0.810	16.2	16.2
SSTL18I	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603	6.7	6.7
SSTL18II	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603	13.4	13.4
SSTL15I[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/40	(V_{DDI} – V_{OH})/40
SSTL15II[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/34	(V_{DDI} – V_{OH})/34
SSTL135I[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/40	(V_{DDI} – V_{OH})/40
SSTL135II[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/34	(V_{DDI} – V_{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V_{DDI} – 0.4	8	8
HSTL15II	1.425	1.5	1.575		0.4	V_{DDI} – 0.4	16	16
HSTL135I[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/50	(V_{DDI} – V_{OH})/50
HSTL135II[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}	V_{OL}/25	(V_{DDI} – V_{OH})/25
HSTL12I[4]	1.14	1.2	1.26		0.1 × V_{DDI}	0.9 × V_{DDI}	V_{OL}/50	(V_{DDI} – V_{OH})/50
HSUL18I[4]	1.71	1.8	1.89		0.1 × V_{DDI}	0.9 × V_{DDI}	V_{OL}/55	(V_{DDI} – V_{OH})/55
HSUL18II[4]	1.71	1.8	1.89		0.1 × V_{DDI}	0.9 × V_{DDI}	V_{OL}/25	(V_{DDI} – V_{OH})/25
HSUL12I[4]	1.14	1.2	1.26		0.1 × V_{DDI}	0.9 × V_{DDI}	V_{OL}/40	(V_{DDI} – V_{OH})/40
POD12I[3,4]	1.14	1.2	1.26		0.5 × V_{DDI}		V_{OL}/48	(V_{DDI} – V_{OH})/48
POD12II[3,4]	1.14	1.2	1.26		0.5 × V_{DDI}		V_{OL}/34	(V_{DDI} – V_{OH})/34

1. V_{OH} is the single-ended high-output voltage.
2. The total DC sink/source current of all IOs within a lane is limited as follows:
    a. HSIO lane: 120 mA per 12 IO buffers.
    b. GPIO lane: 160 mA per 12 IO buffers
3. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).

6.3.4 HSIO On-Die Termination

The following tables lists the on-die termination calibration accuracy specifications for HSIO bank.

Table 18 • Single-Ended Thevenin Termination (Internal Parallel Thevenin Termination)

Min (%)	Typ	Max (%)	Unit	Condition
–40	50	20	Ω	V_{DDI} = 1.8 V/1.5 V/1.35 V/1.2 V
–40	75	20	Ω	V_{DDI} = 1.8 V
–40	150	20	Ω	V_{DDI} = 1.8 V
–20	20	20	Ω	V_{DDI} = 1.5 V/1.35 V
–20	30	20	Ω	V_{DDI} = 1.5 V/1.35 V
–20	40	20	Ω	V_{DDI} = 1.5 V/1.35 V
–20	60	20	Ω	V_{DDI} = 1.5 V/1.35 V
–20	120	20	Ω	V_{DDI} = 1.5 V/1.35 V

Standard	Description	V_L[1]	V_H[1]	V_{ID}[2]	V_{ICM}[2]	V_{MEAS}[3, 4]	V_{REF}[1, 5]	Unit
HSTL135II	Differential HSTL 1.35 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.675	0		V
HSTL12	Differential HSTL 1.2 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
HSUL18I	Differential HSUL 1.8 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
HSUL18II	Differential HSUL 1.8 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
HSUL12	Differential HSUL 1.2 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
POD12I	Differential POD 1.2 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
POD12II	Differential POD 1.2 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.600	0		V
MIPI25	Mobile Industry Processor Interface	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V

1. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst-case of these measurements. V_{REF} values listed are typical. Input waveform switches between V_L and V_H. All rise and fall times must be 1 V/ns.
2. Differential receiver standards all use 250 mV V_{ID} for timing. V_{CM} is different between different standards.
3. Input voltage level from which measurement starts.
4. The value given is the differential input voltage.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models or shown in Output Delay Measurement—Single-Ended Test Setup (see page 27).
6. Emulated bi-directional interface.

7.1.2 Output Delay Measurement Methodology

The following section provides information about the methodology for output delay measurement.

Table 23 • Output Delay Measurement Methodology

Standard	Description	R_{REF} (Ω)	C_{REF} (pF)	V_{MEAS} (V)	V_{REF} (V)
PCI	PCIE 3.3 V	25	10	1.65	
LVTTL33	LVTTL 3.3 V	1M	0	1.65	
LVCMOS33	LVCMOS 3.3 V	1M	0	1.65	
LVCMOS25	LVCMOS 2.5 V	1M	0	1.25	
LVCMOS18	LVCMOS 1.8 V	1M	0	0.90	
LVCMOS15	LVCMOS 1.5 V	1M	0	0.75	
LVCMOS12	LVCMOS 1.2 V	1M	0	0.60	
SSTL25I	Stub-series terminated logic 2.5 V Class I	50	0	V_{REF}	1.25
SSTL25II	SSTL 2.5 V Class II	50	0	V_{REF}	1.25

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

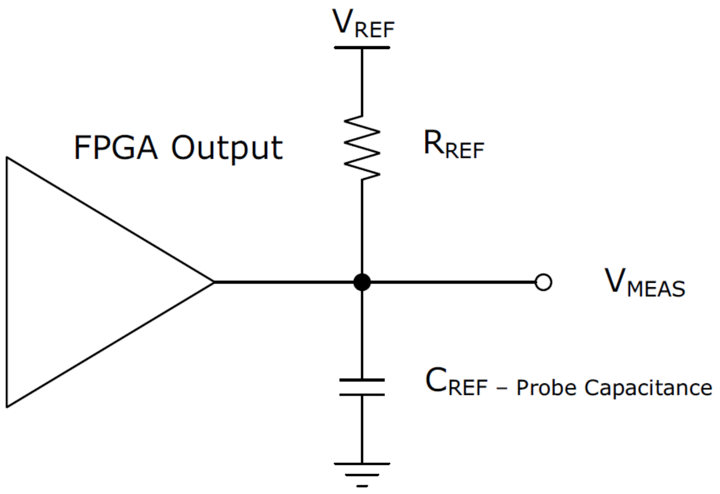
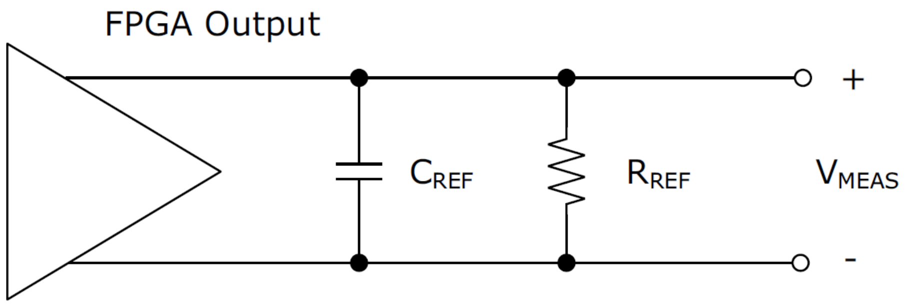


Figure 2 • Output Delay Measurement—Differential Test Setup



7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS18	1250	1250	Mbps
RSDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Standard	STD	–1	Unit
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL12	1066	1333	Mbps
HSTL12	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps

1. Performance is achieved with V_{ID} ≥200 mV.

Table 25 • GPIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS25/LVDS33/LCMDS25/LCMDS33	1250	1600	Mbps
RSDS25/RSDS33	800	800	Mbps
MINILVDS25/MINILVDS33	800	800	Mbps
SUBLVDS25/SUBLVDS33	800	800	Mbps
PPDS25/PPDS33	800	800	Mbps
SLVS25/SLVS33	800	800	Mbps
SLVSE15	800	800	Mbps
HCSL25/HCSL33	800	800	Mbps
BUSLVDSE25	800	800	Mbps
MLVDSE25	800	800	Mbps
LVPECL33	800	800	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
HSTL15I	800	900	Mbps
HSTL15II	800	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
PCI	500	500	Mbps
LVTTL33 (20 mA)	500	500	Mbps
LVCMOS33 (20 mA)	500	500	Mbps
LVCMOS25 (16 mA)	500	500	Mbps

Standard	STD	–1	Unit
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with V_{ID} ≥200 mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3[1]	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3[1]	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3[1]	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2[1]	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2[1]	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2[1]	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2[1]	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2[1]	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
Operating current (V_{DD18})	RC_{SCVPP}			0.1	µA
Operating current (V_{DD})	RC_{SCVDD}			60.7	µA

Parameter	**Symbol**	**STD Min**	**STD Typ**	**STD Max**	**–1 Min**	**–1 Typ**	**–1 Max**	**Unit**
Reference clock input rate[1, 2, 3]	FXCVRREFCLKMAX CASCADE	20		156	20		156	MHz
Reference clock rate at the PFD[4]	FTXREFCLKPFD	20		156	20		156	MHz
Reference clock rate recommended at the PFD for Tx rates 10 Gbps and above[4]	FTXREFCLKPFD10G	75		156	75		156	MHz
Tx reference clock phase noise requirements to meet jitter specifications (156 MHz clock at reference clock input)[5]	FTXREFPN			–110			–110	dBc /Hz
Phase noise at 10 KHz	FTXREFPN			–110			–110	dBc /Hz
Phase noise at 100 KHz	FTXREFPN			–115			–115	dBc /Hz
Phase noise at 1 MHz	FTXREFPN			–135			–135	dBc /Hz
Reference clock input rise time (10%–90%)	TREFRISE		200	500		200	500	ps
Reference clock input fall time (90%–10%)	TREFFALL		200	500		200	500	ps
Reference clock duty cycle	TREFDUTY	40		60	40		60	%
Spread spectrum modulation spread[6]	Mod_Spread	0.1		3.1	0.1		3.1	%
Spread spectrum modulation frequency[7]	Mod_Freq	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	TxREF CLKPFD/ (128)	32	TxREF CLKPFD/ (128*63)	KHz

1. See the maximum reference clock rate allowed per input buffer standard.
2. The minimum value applies to this clock when used as an XCVR reference clock. It does not apply when used as a non-XCVR input buffer (DC input allowed).
3. Cascaded reference clock.
4. After reference clock input divider.
5. Required maximum phase noise is scaled based on actual FTxRefClkPFD value by 20 × log10 (TxRefClkPFD /156 MHz). It is assumed that the reference clock divider of 4 is used for these calculations to always meet the maximum PFD frequency specification.
6. Programmable capability for depth of down-spread or center-spread modulation.
7. Programmable modulation rate based on the modulation divider setting (1 to 63).

7.4.3 Transceiver Reference Clock I/O Standards

The following table describes the differential I/O standards supported as transceiver reference clocks.

Table 48 • Transceiver Differential Reference Clock I/O Standards

I/O Standard	Comment
LVDS25	For DC input levels, se e table Differential DC Input and Output Levels.
HCSL25 (for PCIe)	

Note: The transceiver reference clock differential receiver supports V_{CM} common mode.

7.4.4 Transceiver Interface Performance

The following table describes the single-ended I/O standards supported as transceiver reference clocks.

Table 49 • Transceiver Single-Ended Reference Clock I/O Standards

I/O Standard	Comment
LVCMOS25	For DC input levels, see table DC Input and Output Levels.

7.4.5 Transmitter Performance

The following tables describe performance of the transmitter.

Table 50 • Transceiver Reference Clock Input Termination

Parameter	Symbol	Min	Typ	Max	Unit
Single-ended termination	RefTerm		50		Ω
Single-ended termination	RefTerm		75		Ω
Single-ended termination	RefTerm		150		Ω
Differential termination	RefDiffTerm		115[1]		Ω
Power-up termination			>50K		Ω

1. Measured at VCM= 1.2 V and VID= 350 mV.

Note: All pull-ups are disabled at power-up to allow hot plug capability.

Table 51 • PolarFire Transceiver User Interface Clocks

Parameter	Modes [1]	STD Min	STD Max	–1 Min	–1 Max	Unit
Transceiver TX_CLK range (non-deterministic PCS mode with global or regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		325		325	MHz
	40-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		260		320	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		165		160	MHz
	80-bit, max data rate = 10.3125 Gbps(–STD) / 12.7 Gbps (–1)[1]		130		130	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz
	8-bit, max data rate = 1.6 Gbps		200		200	MHz

Table 60 • 10GbE (RXAUI)

	Data Rate	Min	Max	Unit
Total transmit jitter	6.25 Gbps			UI
Receiver jitter tolerance	6.25 Gbps			UI

7.5.4 1GbE (1000BASE-T)

The following table describes 1GbE (1000BASE-T).

Table 61 • 1GbE (1000BASE-T)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

The following table describes 1GbE (1000BASE-X).

Table 62 • 1GbE (1000BASE-X)

	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps			UI
Receiver jitter tolerance	1.25 Gbps			UI

7.5.5 SGMII and QSGMII

The following table describes SGMII.

Table 63 • SGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	1.25 Gbps		0.24	UI
Receiver jitter tolerance	1.25 Gbps	0.749		UI

The following table describes QSGMII.

Table 64 • QSGMII

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	5.0 Gbps		0.3	UI
Receiver jitter tolerance	5.0 Gbps	0.65		UI

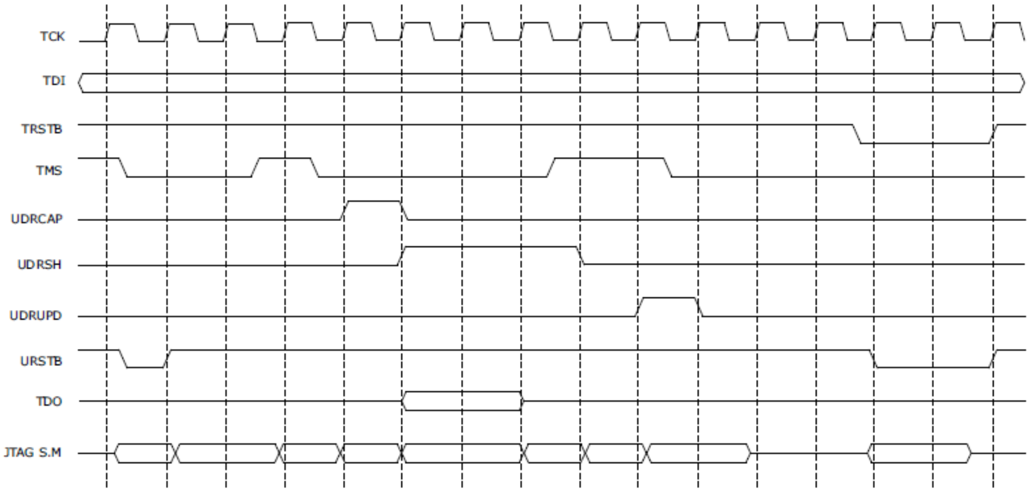
7.5.6 SDI

The following table describes SDI.

Table 65 • SDI

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter				UI
Receiver jitter tolerance				UI

Figure 3 • UJTAG Timing Diagram



7.8.2 UJTAG_SEC Switching Characteristics

The following table describes characteristics of UJTAG_SEC switching.

Table 89 • UJTAG Security Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F_{TCK}				MHz	

7.8.3 USPI Switching Characteristics

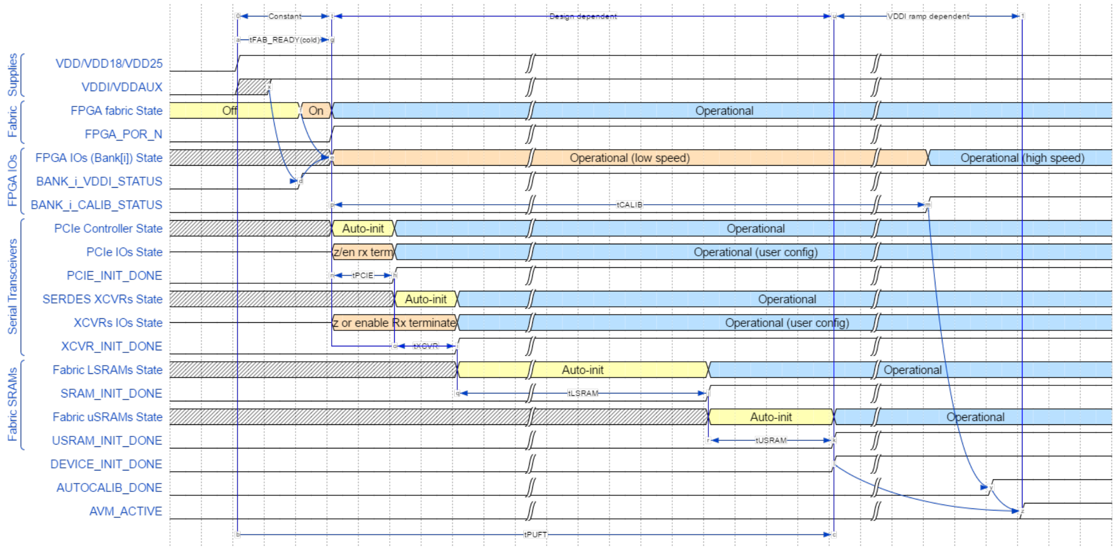
The following section describes characteristics of USPI switching.

Table 90 • SPI Macro Interface Timing Characteristics

Parameter	Symbol	V_{DDI} = 3.3 V Max	V_{DDI} = 2.5 V Max	V_{DDI} = 1.8 V Max	V_{DDI} = 1.5 V Max	V_{DDI} = 1.2 V Max	Unit
Propagation delay from the fabric to pins[1]	TPD_MOSI	0.8	1	1.2	1.4	1.6	ns
	TPD_MISO	3.5	3.75	4	4.25	4.5	ns
	TPD_SS	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK	3.5	3.75	4	4.25	4.5	ns
	TPD_MOSI_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SS_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK_OE	3.5	3.75	4	4.25	4.5	ns

1. Assumes CL of the relevant I/O standard as described in the input and output delay measurement tables.

Figure 5 • Cold Reset Timing



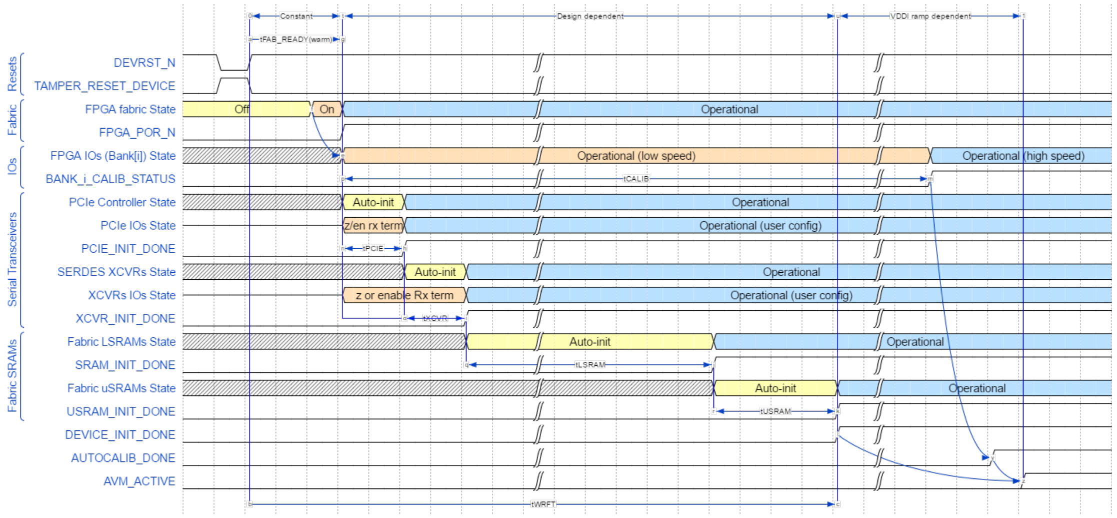
Notes:

- The previous diagram showsthe case where VDDI/VDDAUX of I/O banks are powered either before or sufficiently soon after VDD/VDD18/VDD25 that the I/O bank enable time is measured from the assertion time of VDD/VDD18/VDD25 (that is, the PUFT specification). If VDDI/VDDAUX of I/O banks are powered sufficiently after VDD/VDD18/VDD25, then the I/O bank enable time is measured from the assertion of VDDI/VDDAUX and is not specified by the PUFT specification. In this case, I/O operation is indicated by the assertion of BANK_i_VDDI_STATUS, rather than being measured relative to FABRIC_POR_N negation.
- AUTOCALIB_DONE assertion indicates the completion of calibration for any I/O banks specified by the user for auto-calibration. AUTOCALIB_DONE asserts independently of DEVICE_INIT_DONE. It may assert before or after DEVICE_INIT_DONE and is determined by the following:
  - How long after VDD/VDD18/VDD25 that VDDI/VDDAUX are powered on. Note that if any of the user-specified I/O banks are not powered on within the auto-calibration timeout window, then AUTOCALIB_DONE doesn't assert until after this timeout.
  - The specified ramp times of VDDI of each I/O bank designated for auto-calibration.
  - How much auto-initialization is to be performed for the PCIe, SERDES transceivers, and fabric LSRAMs.
- If any of the I/O banks specified for auto-calibration do not have their VDDI/VDDAUX powered on within the auto-calibration timeout window, then it will be approximately auto-calibrated whenever VDDI/VDDAUX is subsequently powered on. To obtain an accurate calibration however, on such IO banks, it is necessary to initiate a re-calibration (using CALIB_START from fabric).
- AVM_ACTIVE only asserts if avionics mode is being used. It is asserted when the later of DEVICE_INIT_DONE or AUTOCALIB_DONE assert.

7.9.2 Warm Reset Initialization Sequence

The following warm reset timing diagram shows the initialization sequencing of the device when either DEVRST_N or TAMPER_RESET_DEVICE signals are asserted.

Figure 6 • Warm Reset Timing



7.9.3 Power-On Reset Voltages

7.9.3.1 Main Supplies

The start of power-up to functional time (T_{PUFT}) is defined as the point at which the latest of the main supplies (VDD, VDD18, VDD25) reach the reference voltage levels specified in the following table. This starts the process of releasing the reset of the device and powering on the FPGA fabric and IOs.

Table 97 • POR Ref Voltages

Supply	Power-On Reset Start Point (V)	Note
VDD	0.95	Applies to both 1.0 V and 1.05 V operation.
VDD18	1.71	
VDD25	2.25	

7.9.3.2 I/O-Related Supplies

For the I/Os to become functional (for low speed, sub 400 MHz operation), the (per-bank) I/O supplies (VDDI, VDDAUX) must reach the trip point voltage levels specified in the following table and the main supplies above must also be powered on.

Table 98 • I/O-Related Supplies

Supply	I/O Power-Up Start Point (V)
VDDI	0.85
VDDAUX	1.6

There are no sequencing requirements for the power supplies. However, VDDI3 and must be valid at same time as the main supplies. The other IO supplies (VDDI, VDDAUX) have no effect on power-up of FPGA fabric (that is, the fabric still powers up even if the IO supplies of some IO banks remain powered off).

Table 101 • Cold and Warm Boot

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from T_{FAB_READY} to ready to program through JTAG/SPI-Slave		0	0	0	ms	
The time from T_{FAB_READY} to auto-update start			T_{PUF_OVHD}[1]	T_{PUF_OVHD}[1]	ms	
The time from T_{FAB_READY} to programming recovery start			T_{PUF_OVHD}[1]	T_{PUF_OVHD}[1]	ms	
The time from T_{FAB_READY} to the tamper flags being available	T_{TAMPER_READY}	0	0	0	ms	
The time from T_{FAB_READY} to the Athena Crypto co-processor being available (for S devices only)	T_{CRYPTO_READY}	0	0	0	ms	

[1] Programming depends on the PUF to power up. Refer to T_{PUF_OVHD} at section Secure NVM Performance (see page 58).

7.9.8 I/O Calibration

The following tables specify the initial I/O calibration time for the fastest and slowest supported VDDI ramp times of 0.2 ms to 50 ms, respectively. This only applies to I/O banks specified by the user to be auto-calibrated.

Table 102 • I/O Initial Calibration Time (TCALIB)

Ramp Time	Min (ms)	Max (ms)	Condition
0.2 ms	0.98	2.63	Applies to HSIO and GPIO banks
50 ms	41.62	62.19	Applies to HSIO and GPIO banks

Notes:

- The user may specify any VDDI ramp time in the range specified above. The nominal initial calibration time is given by the specified VDDI ramp time plus 2 ms.
- In order for IO calibration to start, VDDI and VDDAUX of the I/O bank must be higher than the trip point levels specified in I/O-Related Supplies (see page 66).

Table 103 • I/O Fast Recalibration Time (TRECALIB)

I/O Type	Min (ms)	Typ (ms)	Max (ms)	Condition
GPIO bank	0.16	0.20	0.24	GPIO configured for 3.3 V operation
HSIO bank	0.20	0.25	0.30	HSIO configured for 1.8 V operation

Note: In order to obtain fast re-calibration, the user must assert the relevant clock request signal from the FPGA fabric to the I/O bank controller.

The following table describes the time to enter Flash*Freeze Mode and to exit Flash*Freeze mode.

Table 104 • Flash*Freeze

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from Flash*Freeze entry command to the Flash*Freeze state	T_{FF_ENTRY}		59		µs	
The time from Flash*Freeze exit pin assertion to fabric operational state	$T_{FF\_FABRIC\_UP}$		133		µs	
The time from Flash*Freeze exit pin assertion to I/Os operational	$T_{FF\_IO\_ACTIVE}$		143		µs	

7.10 Dedicated Pins

The following section describes the dedicated pins.

7.10.1 JTAG Switching Characteristics

The following table describes characteristics of JTAG switching.

Table 105 • JTAG Electrical Characteristics

Symbol	Description	Min	Typ	Max	Unit	Condition
T_{DISU}	TDI input setup time	0.0			ns	
T_{DIHD}	TDI input hold time	2.0			ns	
T_{TMSSU}	TMS input setup time	1.5			ns	
T_{TMSHD}	TMS input hold time	1.5			ns	
F_{TCK}	TCK frequency			25	MHz	
T_{TCKDC}	TCK duty cycle	40		60	%	
T_{TDOCQ}	TDO clock to Q out			8.4	ns	C_{LOAD} = 40 pf
T_{RSTBCQ}	TRSTB clock to Q out			23.5	ns	C_{LOAD} = 40 pf
T_{RSTBPW}	TRSTB min pulse width	50			ns	
$T_{RSTBREM}$	TRSTB removal time	0.0			ns	
$T_{RSTBREC}$	TRSTB recovery time	12.0			ns	
CIN_{TDI}	TDI input pin capacitance			5.3	pf	
CIN_{TMS}	TMS input pin capacitance			5.3	pf	
CIN_{TCK}	TCK input pin capacitance			5.3	pf	
CIN_{TRSTB}	TRSTB input pin capacitance			5.3	pf	

7.10.2 SPI Switching Characteristics

The following tables describe characteristics of SPI switching.

Table 106 • SPI Master Mode (PolarFire Master) During Programming

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{MSCK}			20	MHz	

Table 107 • SPI Master Mode (PolarFire Master) During Device Initialization

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{MSCK}			40	MHz	

Table 108 • SPI Slave Mode (PolarFire Slave)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{SSCK}			80	MHz	

7.10.3 SmartDebug Probe Switching Characteristics

The following table describes characteristics of SmartDebug probe switching.

Table 109 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V – 1	Unit
Maximum frequency of probe signal	F_{MAX}	100	100	100	100	MHz
Minimum delay of probe signal	T_{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T_{Max_delay}	13	12	13	12	ns

7.10.4 DEVRST_N Switching Characteristics

The following table describes characteristics of DEVRST_N switching.

Table 110 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR_{RAMP}		10		µs	It must be a normal clean digital signal, with typical rise and fall times
DEVRST_N assert time	DR_{ASSERT}	1			µs	The minimum time for DEVRST_N assertion to be recognized
DEVRST_N de-assert time	$DR_{DEASSERT}$	2.75			ms	The minimum time DEVRST_N needs to be de-asserted before assertion

7.10.5 FF_EXIT Switching Characteristics

The following table describes characteristics of FF_EXIT switching.

Table 111 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF_{RAMP}		10		µs	
Minimum FF_EXIT_N assert time	FF_{ASSERT}	1			µs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	$FF_{DEASSERT}$	170			µs	The minimum time FF_EXIT_N needs to be de-asserted before assertion